## IN THE CLAIMS:

Claim 1 (Currently Amended) A method of fabricating a liquid crystal display device, comprising the steps of:

forming a first metal layer on a substrate to form a gate line including a gate electrode, a gate pad, and a first capacitor electrode;

forming a first insulating layer, a second insulating layer, an active layer, and a second metal layer on the substrate;

patterning the second metal layer to form a data line including a data pad, a source electrode, a drain electrode, and a second capacitor electrode;

forming a passivation layer on the substrate;

forming a photoresist on the passivation layer;

exposing the photoresist using a mask having a plurality of light shielding portions, a plurality of light transmissive portions, and a plurality of semi-transmissive portions;

forming a plurality of first photoresist portions, a plurality of second photoresist portions, and a plurality of third photoresist portions, wherein the first photoresist portions correspond to portions of a thin film transistor, the data line, the second capacitor electrode, the second photoresist portions correspond to portions of the gate pad, portions of the data pad, portions of the second capacitor electrode, the third photoresist portions correspond to a pixel region, portions of the gate pad, portions of the source

electrode, portions of the drain electrode, and wherein the first photoresist portions correspond to the plurality of light shielding portions, the second photoresist portions correspond to the plurality of light transmissive portions, and the third photoresist portions correspond to the plurality of semi-transmissive portions;

patterning the passivation layer, the active layer, the first insulating layer and the second insulating layer; and

forming a pixel electrode on the passivation layer, wherein the pixel electrode contacts a side edge portions of the drain electrode.

Claim 2 (Previously Presented) The method of fabricating a liquid crystal display device according to Claim 1, wherein the gate line and the data line cross with each other to define the pixel region, and the source electrode and the drain electrode are spaced apart from each other.

Claim 3 (Original) The method of fabricating a liquid crystal display device according to Claim 1, wherein the step of depositing and patterning a first metal layer includes a first masking step.

Claim 4 (Previously Presented) The method of fabricating a liquid crystal display device according to Claim 1, wherein the step of depositing a first insulating layer, a second insulating layer, an active layer, and a second metal layer includes a second masking step.

Claim 5 (Original) The method of fabricating a liquid crystal display device according to

Claim 4, wherein the step of patterning the second metal layer is included in the second

masking step.

Claim 6 (Original) The method of fabricating a liquid crystal display device according to

Claim 1, wherein the steps of forming a passivation layer, forming a photoresist, exposing

the photoresist, forming first, second and third photoresist portions, and patterning the

passivation layer are included in a third masking step.

Claim 7 (Previously Presented) The method of fabricating a liquid crystal display device

according to Claim 6, wherein, in the third masking step, a side portion and upper

surfaces of the drain electrode are uncovered, a capacitor contact hole is formed over the

second capacitor electrode, and a data pad contact hole is formed over the data pad

through the passivation layer, and a gate pad contact hole is formed over the gate pad

passing through the first insulating layer, the second insulating layer, the active layer, and

the passivation layer.

Claim 8 (Previously Presented) The method of fabricating a liquid crystal display device

according to Claim 1, wherein each of the third photoresist portions have a thickness of

800 to 900 Å.

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Claim 9 (Original) The method of fabricating a liquid crystal display device according to Claim 1, wherein the first metal layer includes at least a first aluminum neodymium

(AlNd) material layer and a second molybdenum (Mo) material layer.

Claim 10 (Previously Presented) The method of fabricating a liquid crystal display device according to Claim 1, wherein the first insulating layer, the second insulating layer and the passivation layer include at least an inorganic insulating material.

Claim 11 (Original) The method of fabricating a liquid crystal display device according to Claim 10, wherein the inorganic insulating material includes at least one material selected from a group consisting of silicon oxide (SiO<sub>2</sub>) and silicon nitride (SiN<sub>X</sub>).

Claim 12 (Previously Presented) The method of fabricating a liquid crystal display device according to Claim 1, wherein the first insulating layer, the second insulating layer and the passivation layer include at least organic insulating materials.

Claim 13 (Original) The method of fabricating a liquid crystal display device according to Claim 12, wherein the organic insulating materials include at least one material selected from a group consisting benzocyclobutene (BCB) and an acryl-based resin.

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Claim 14 (Original) The method of fabricating a liquid crystal display device according to

Claim 1, wherein a portion of the passivation layer disposed over the data line has a width

smaller than a corresponding width of the data line.

Claim 15 (Previously Presented) The method of fabricating a liquid crystal display device

according to Claim 1, wherein the light shielding portions of the mask include at least an

opaque metal material having a low reflectivity.

Claim 16 (Original) The method of fabricating a liquid crystal display device according to

Claim 15, wherein the opaque metal includes at least a chromium (Cr) material.

Claim 17 (Original) The method of fabricating a liquid crystal display device according to

Claim 1, wherein the semi-transmissive portion of the mask includes at least a

molybdenum silicide (MoSi) material.

Claims 18-28 (Canceled).